

1 **ABSTRACT OF THE DISCLOSURE**

2 The invention includes a method of forming a capacitor structure.
3 A first electrical node is formed, and a layer of metallic aluminum is
4 formed over the first electrical node. Subsequently, an entirety of the
5 metallic aluminum within the layer is transformed into one or more of
6 AlN, AlON, and AlO, with the transformed layer being a dielectric
7 material over the first electrical node. A second electrical node is then
8 formed over the dielectric material. The first electrical node, second
9 electrical node and dielectric material together define at least a portion
10 of the capacitor structure. The invention also pertains to a capacitor
11 structure which includes a first electrical node, a second electrical node,
12 and a dielectric material between the first and second electrical nodes.
13 The dielectric material consists essentially of aluminum, oxygen and
14 nitrogen.